



8N50H

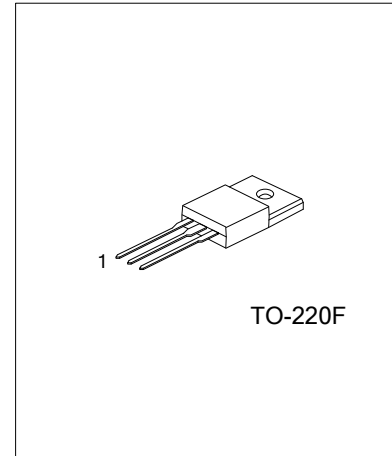
Power MOSFET

8A, 500V N-CHANNEL POWER MOSFET

DESCRIPTION

The UTC **8N50H** is an N-channel mode power MOSFET using UTC's advanced technology to provide customers with planar stripe and DMOS technology. This technology allows a minimum on-state resistance and superior switching performance. It also can withstand high energy pulse in the avalanche and commutation mode.

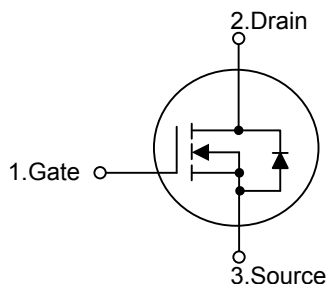
The UTC **8N50H** is generally applied in high efficiency switch mode power supplies, active power factor correction and electronic lamp ballasts based on half bridge topology.



FEATURES

- * $R_{DS(ON)}=0.8\Omega$ @ $V_{GS}=10V$
- * High Switching Speed
- * 100% Avalanche Tested

SYMBOL



ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
8N50HL-TF3-T	8N50HG-TF3-T	TO-220F	G	D	S	Tube

Note: Pin Assignment: G: Gate D: Drain S: Source

<p>8N50HL-TA3-T</p> <p>(1)Packing Type</p> <p>(2)Package Type</p> <p>(3)Lead Free</p>		<p>(1) T: Tube</p> <p>(2) TF3: TO-220F</p> <p>(3) G: Halogen Free, L: Lead Free</p>
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■ ABSOLUTE MAXIMUM RATINGS ($T_C=25^\circ\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT
Drain-Source Voltage	V_{DSS}	500	V
Gate-Source Voltage	V_{GSS}	± 30	V
Drain Current	I_D	7 (Note 2)	A
Avalanche Current (Note 3)	I_{AR}	7	A
Single Pulsed Avalanche Energy (Note 4)	E_{AS}	270	mJ
Power Dissipation	P_D		W
Junction Temperature	T_J	+150	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55~+150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Drain current limited by maximum junction temperature

3. Repetitive Rating: Pulse width limited by maximum junction temperature

4. $L = 10\text{mH}$, $I_{AS} = 8\text{A}$, $V_{DD} = 50\text{V}$, $R_G = 25\Omega$, Starting $T_J = 25^\circ\text{C}$

■ THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	θ_{JA}		$^\circ\text{C/W}$
Junction to Case	θ_{JC}		$^\circ\text{C/W}$

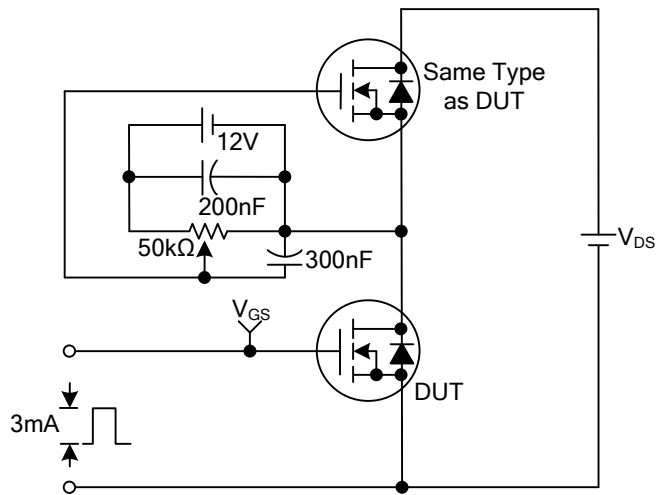
■ ELECTRICAL CHARACTERISTICS ($T_C=25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV _{DSS}	I _D =250μA, V _{GS} =0V	500			V
Drain-Source Leakage Current		I _{DSS}	V _{DS} =500V, V _{GS} =0V			1	μA
Gate- Source Leakage Current	Forward	I _{GSS}	V _{GS} =+30V, V _{DS} =0V			+100	nA
	Reverse		V _{GS} =-30V, V _{DS} =0V			-100	nA
ON CHARACTERISTICS							
Gate Threshold Voltage		V _{GS(TH)}	V _{DS} =V _{GS} , I _D =250μA	2.0		4.0	V
Static Drain-Source On-State Resistance		R _{DS(ON)}	V _{GS} =10V, I _D =3.5A		0.8	1	Ω
DYNAMIC PARAMETERS							
Input Capacitance		C _{ISS}	V _{GS} =0V, V _{DS} =25V, f=1.0MHz				pF
Output Capacitance		C _{OSS}					pF
Reverse Transfer Capacitance		C _{RSS}					pF
SWITCHING PARAMETERS							
Total Gate Charge		Q _G	V _{DD} =50V, I _D =1.3A, I _G =100uA, V _{GS} =10V (Note 1, 2)		12.8	16.6	nC
Gate to Source Charge		Q _{GS}			3.7		nC
Gate to Drain Charge		Q _{GD}			5.8		nC
Turn-ON Delay Time		t _{D(ON)}	V _{DD} =30V, I _D =0.5A, R _G =25Ω, V _{GS} =0~10V (Note 1, 2)		6	20	ns
Rise Time		t _R			55	120	ns
Turn-OFF Delay Time		t _{D(OFF)}			25	60	ns
Fall-Time		t _F			35	80	ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS							
Maximum Body-Diode Continuous Current		I _S				7	A
Drain-Source Diode Forward Voltage		V _{SD}	I _S =7A, V _{GS} =0V			1.4	V

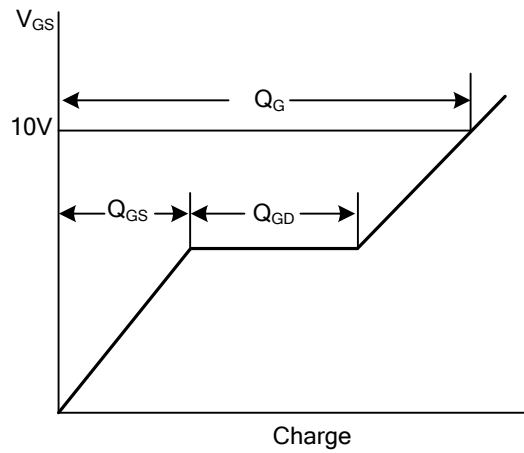
Notes: 1. Pulse Test: Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$

2. Essentially independent of operating temperature

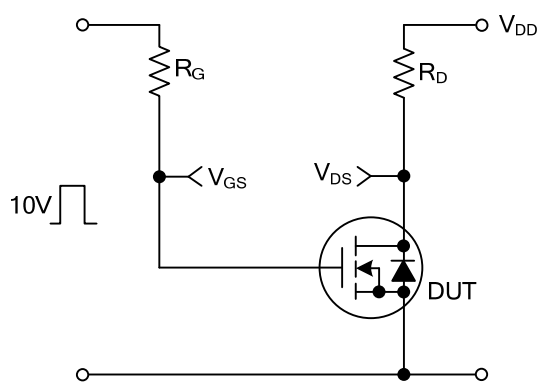
■ TEST CIRCUITS AND WAVEFORMS



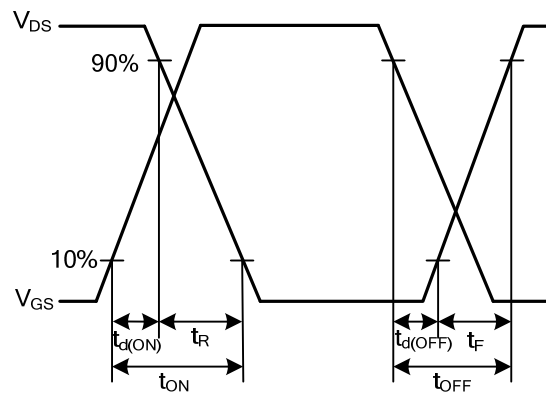
Gate Charge Test Circuit



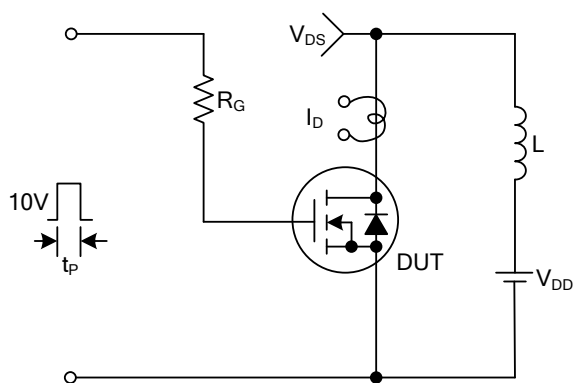
Gate Charge Waveforms



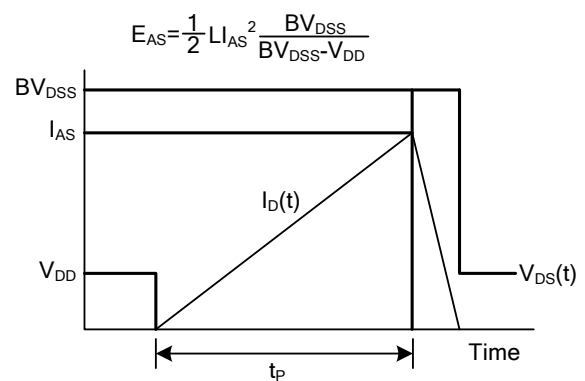
Resistive Switching Test Circuit



Resistive Switching Waveforms

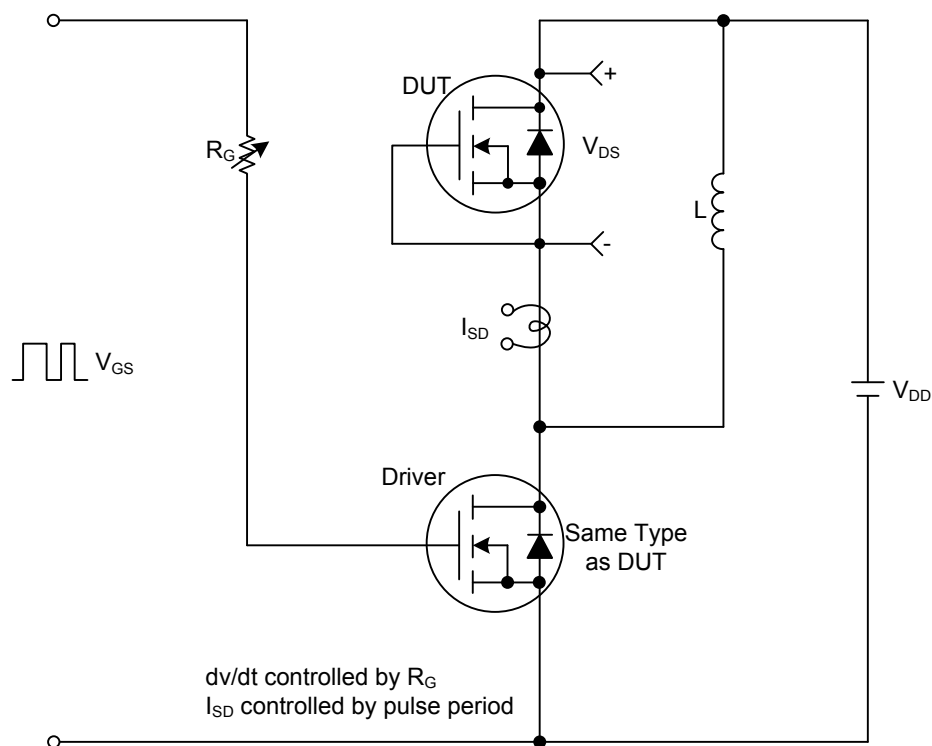


Unclamped Inductive Switching Test Circuit

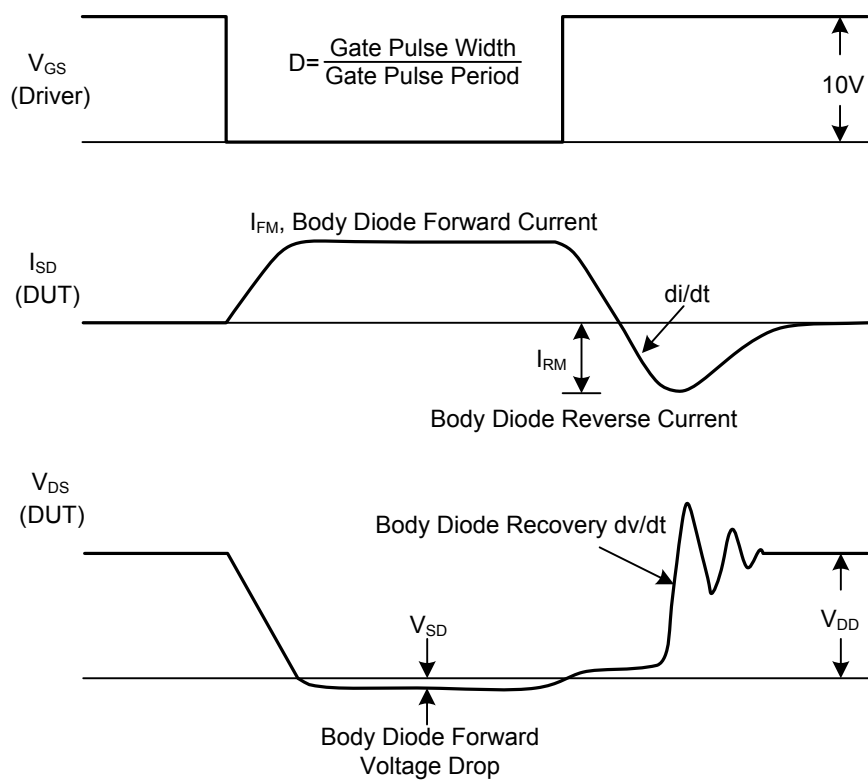


Unclamped Inductive Switching Waveforms

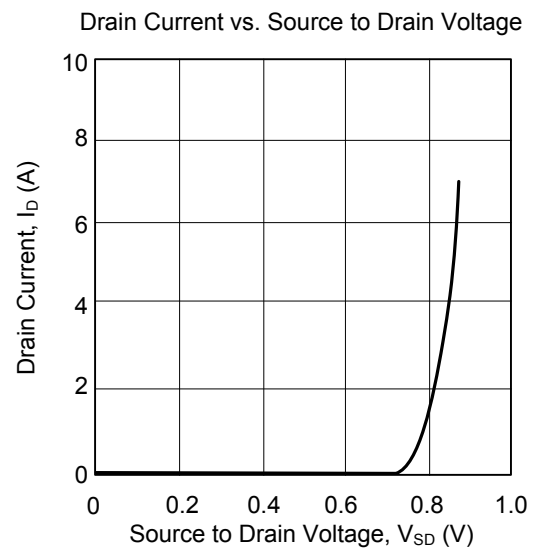
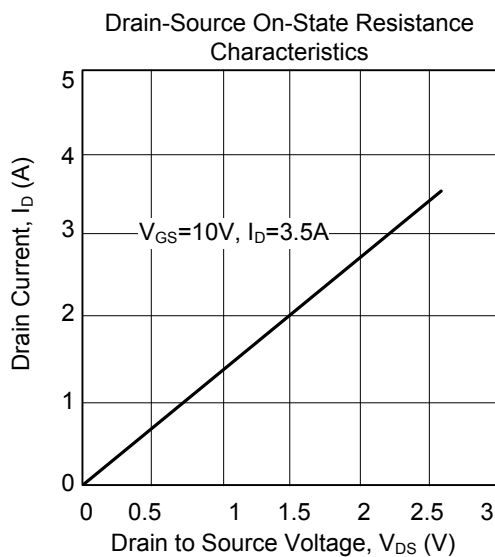
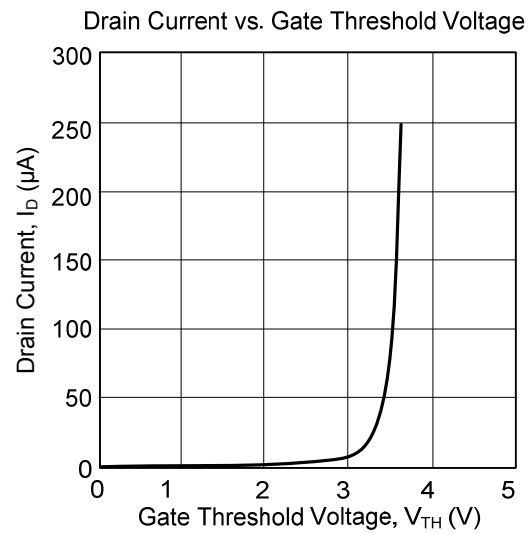
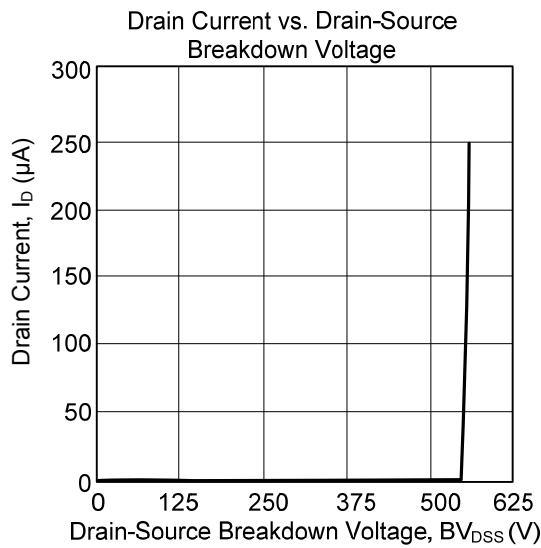
■ TEST CIRCUITS AND WAVEFORMS(Cont.)



Peak Diode Recovery dv/dt Test Circuit & Waveforms



■ TYPICAL CHARACTERISTICS



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